

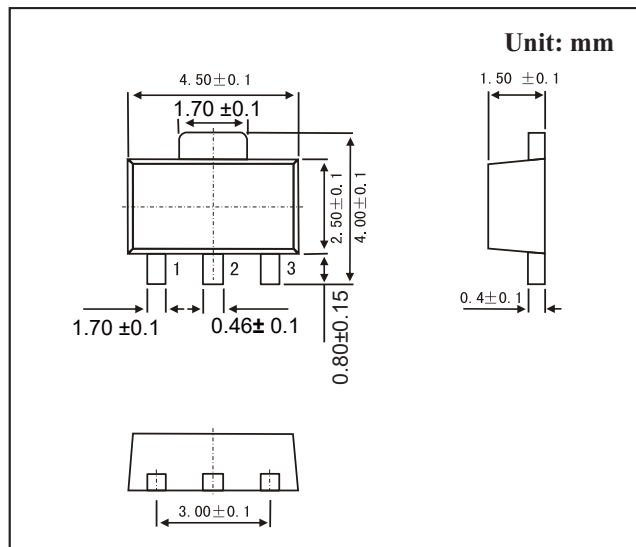
SOT-89 Plastic-Encapsulate Transistors

FEATURES

- High voltage: $V_{CEO}=160V$
- Large continuous collector current
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-89 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	160	V
Collector - Emitter Voltage	V_{CEO}	160	
Emitter - Base Voltage	V_{EBO}	6	
Collector Current - Continuous	I_C	1	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu A, I_E = 0$	160			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 10 mA, I_B = 0$	160			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu A, I_C = 0$	6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 150 V, I_E = 0$			1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6 V, I_C = 0$			1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 mA, I_B = 50 mA$			1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500 mA, I_B = 50 mA$			1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = 5 V, I_C = 5 mA$	0.45		0.75	
DC current gain	h_{FE}	$V_{CE} = 6 V, I_C = 200 mA$	100		320	
Collector output capacitance	C_{ob}	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$			20	pF
Transition frequency	f_T	$V_{CE} = 5 V, I_C = 200 mA$	20			MHz

RATINGS AND CHARACTERISTIC CURVES

